

## PNP DUAL SILICON TRANSISTOR

Qualified per MIL-PRF-19500/496

### Devices

2N5795

2N5796  
2N5796U

### Qualified Level

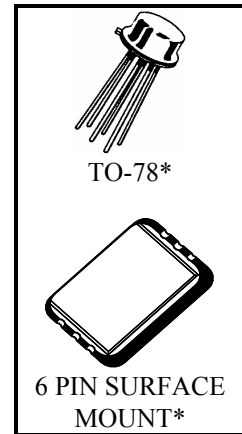
JAN  
JANTX  
JANTXV

### MAXIMUM RATINGS

Ratings	Symbol	Value		Units
Collector-Emitter Voltage	$V_{CEO}$	60		Vdc
Collector-Base Voltage	$V_{CBO}$	60		Vdc
Emitter-Base Voltage	$V_{EBO}$	5.0		Vdc
Collector Current	$I_C$	600		mAdc
		<b>One<sup>(1)</sup> Section</b>	<b>Both<sup>(2)</sup> Sections</b>	
Total Power Dissipation @ $T_A = +25^{\circ}\text{C}$	$P_T$	0.5	0.6	W
Operating & Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +175		$^{\circ}\text{C}$

1) Derate linearly 2.86 mW/ $^{\circ}\text{C}$  for  $T_A \geq +25^{\circ}\text{C}$

2) Derate linearly 3.43 mW/ $^{\circ}\text{C}$  for  $T_A \geq +25^{\circ}\text{C}$



\*See MILPRF19500/496 for package outline

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
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### OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage $I_C = 10 \text{ mAdc}$	$V_{(BR)CEO}$	60		Vdc
Collector-Base Cutoff Current $V_{CB} = 50 \text{ Vdc}$ $V_{CBO} = 60 \text{ Vdc}$	$I_{CBO}$		10 10	$\eta\text{Adc}$ $\mu\text{Adc}$
Emitter-Base Cutoff Current $V_{EB} = 3.0 \text{ Vdc}$ $V_{EB} = 5.0 \text{ Vdc}$	$I_{EBO}$		100 10	$\eta\text{Adc}$ $\mu\text{Adc}$

**2N5795, 2N5796 JAN SERIES**

**ELECTRICAL CHARACTERISTICS (con't)**

Characteristics	Symbol	Min.	Max.	Unit
<b>ON CHARACTERISTICS (1)</b>				
Forward-Current Transfer Ratio $I_C = 100 \mu\text{A dc}, V_{CE} = 10 \text{ V dc}$ $I_C = 1.0 \text{ mA dc}, V_{CE} = 10 \text{ V dc}$ $I_C = 10 \text{ mA dc}, V_{CE} = 10 \text{ V dc}$ $I_C = 150 \text{ mA dc}, V_{CE} = 10 \text{ V dc}$ $I_C = 300 \text{ mA dc}, V_{CE} = 10 \text{ V dc}$ $I_C = 150 \text{ mA dc}, V_{CE} = 1.0 \text{ V dc}$	2N5795	40 40 40 40 20 20	150	
$I_C = 100 \mu\text{A dc}, V_{CE} = 10 \text{ V dc}$ $I_C = 1.0 \text{ mA dc}, V_{CE} = 10 \text{ V dc}$ $I_C = 10 \text{ mA dc}, V_{CE} = 10 \text{ V dc}$ $I_C = 150 \text{ mA dc}, V_{CE} = 10 \text{ V dc}$ $I_C = 300 \text{ mA dc}, V_{CE} = 10 \text{ V dc}$ $I_C = 150 \text{ mA dc}, V_{CE} = 1.0 \text{ V dc}$	2N5796 2N5796U	75 100 100 100 50 50	300	
Collector-Emitter Saturation Voltage $I_C = 150 \text{ mA dc}, I_B = 15 \text{ mA dc}$ $I_C = 500 \text{ mA dc}, I_B = 50 \text{ mA dc}$	$V_{CE(sat)}$		0.4 1.6	Vdc
Base-Emitter Saturation Voltage $I_C = 150 \text{ mA dc}, I_B = 15 \text{ mA dc}$ $I_C = 500 \text{ mA dc}, I_B = 50 \text{ mA dc}$	$V_{BE(sat)}$		1.3 2.6	Vdc

**DYNAMIC CHARACTERISTICS**

Magnitude of Small-Signal Forward Current Transfer Ratio $I_C = 20 \text{ mA dc}, V_{CE} = 20 \text{ V dc}, f = 100 \text{ MHz}$	$ h_{fe} $	2.0	10	
Output Capacitance $V_{CB} = 10 \text{ V dc}, I_E = 0, 100 \text{ kHz} \leq f \leq 1.0 \text{ MHz}$	$C_{obo}$		8.0	pF
Input Capacitance $V_{EB} = 2.0 \text{ V dc}, I_C = 0, 100 \text{ kHz} \leq f \leq 1.0 \text{ MHz}$	$C_{ibo}$		25	pF

**SWITCHING CHARACTERISTICS**

Turn-On Time $V_{CC} = 30 \text{ V dc}; I_C = 150 \text{ mA dc}; I_{B1} = 15 \text{ mA dc}$	$t_{on}$		50	ns
Turn-Off Time $V_{CC} = 30 \text{ V dc}; I_C = 150 \text{ mA dc}; I_{B1} = I_{B2} = 15 \text{ mA dc}$	$t_{off}$		140	ns

1) Pulse Test: Pulse Width = 300 $\mu$ s, Duty Cycle  $\leq$  2.0%.